NIKO-SEM

P-Channel Logic Level Enhancement Mode Field Effect Transistor

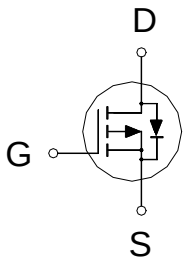
P2003EVG

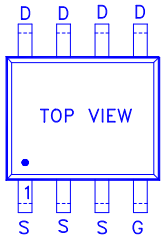
SOP-8

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
-30	20mΩ	-9A





4 :GATE
5,6,7,8 :DRAIN
1,2,3 :SOURCE

100% UIS tested

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±25	V
Continuous Drain Current	T_C = 25 °C	I_D	-9	A
	T_C = 70 °C		-7	
Pulsed Drain Current[1]		I_{DM}	-50	
Avalanche Current		I_{AS}	-26	
Avalanche Energy	L = 0.1mH	E_{AS}	34	mJ
Power Dissipation	T_C = 25 °C	P_D	2.5	W
	T_C = 70 °C		1.6	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Case	$R_{\theta JC}$		25	°C / W
Junction-to-Ambient	$R_{\theta JA}$		50	°C / W

[1]Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS (T_C = 25 °C, Unless Otherwise Noted)

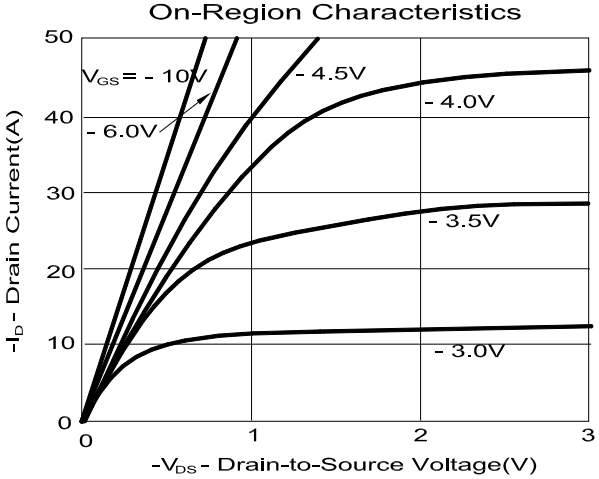
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS MIN	LIMITS TYP	LIMITS MAX	UNIT
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250μA	-30			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250μA	-1	-1.5	-3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±25V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -24V, V_{GS} = 0V			-1	μA
		V_{DS} = -20V, V_{GS} = 0V, T_J = 125 °C			-10	
On-State Drain Current[1]	$I_{D(ON)}$	V_{DS} = -5V, V_{GS} = -10V	9			A
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = -4.5V, I_D = -7A		25	35	mΩ
		V_{GS} = -10V, I_D = -9A		15	20	

Forward Transconductance[1]	g_{fs}	V_{DS} = -10V, I_D = -9A		24		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -15V, f = 1MHz		1610		pF
Output Capacitance	C_{oss}			410		
Reverse Transfer Capacitance	C_{rss}			200		
Gate Resistance	Rg	V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz		3.7		Ω
Total Gate Charge[2]	Q_g	V_{DS} = 0.5$V_{(BR)DSS}$, V_{GS} = -10V, I_D = -9A		31.4		nC
Gate-Source Charge[2]	Q_{gs}			4.5		
Gate-Drain Charge[2]	Q_{gd}			8.2		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = -15V, R_L = 1Ω, I_D ≅ -1A, V_{GS} = -10V, R_{GS} = 6Ω		5.7		nS
Rise Time[2]	t_r			10		
Turn-Off Delay Time[2]	$t_{d(off)}$			18		
Fall Time[2]	t_f			5		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25 °C)						
Continuous Current	I_S				-2.1	A
Forward Voltage[1]	V_{SD}	I_F = -1A, V_{GS} = 0V			-1.2	V

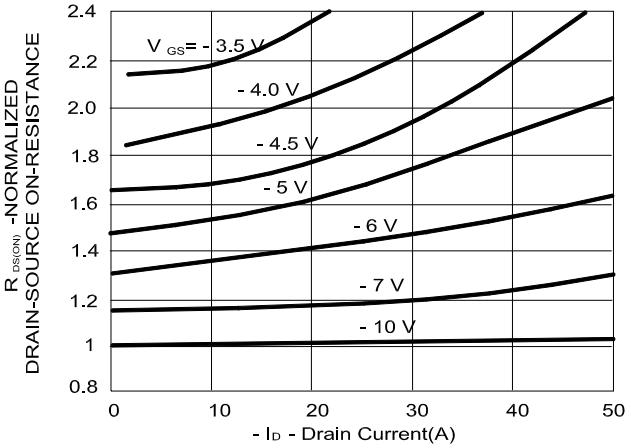
[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

REMARK: THE PRODUCT MARKED WITH "P2003EVG", DATE CODE or LOT #

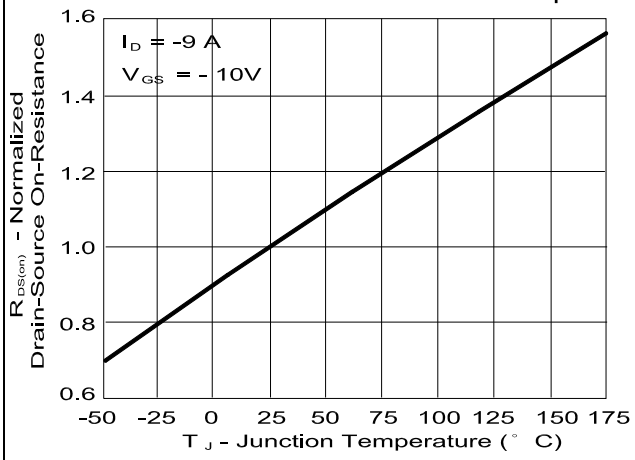
On-Region Characteristics



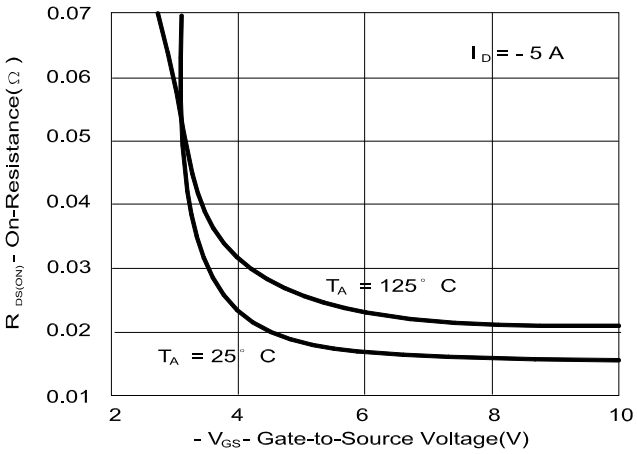
On-Resistance Variation with Drain Current and Gate Voltage



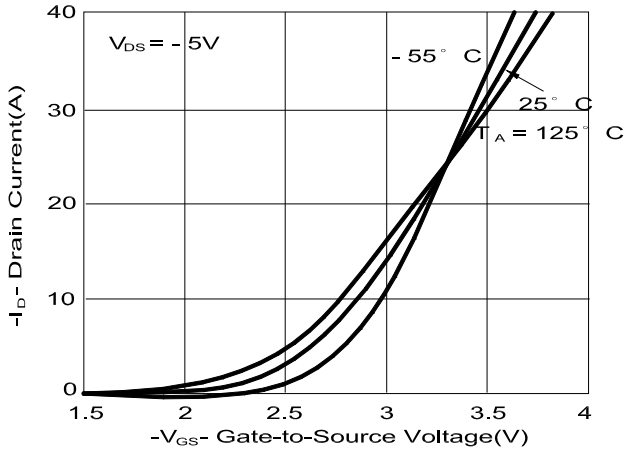
On-Resistance Variation with Temperature



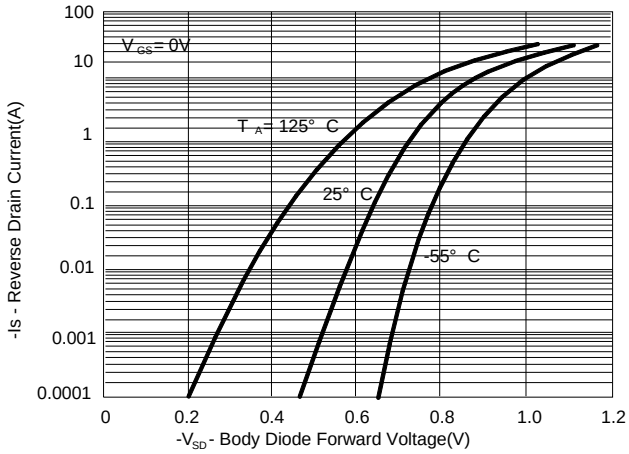
On-Resistance Variation with Gate-to-Source Voltage



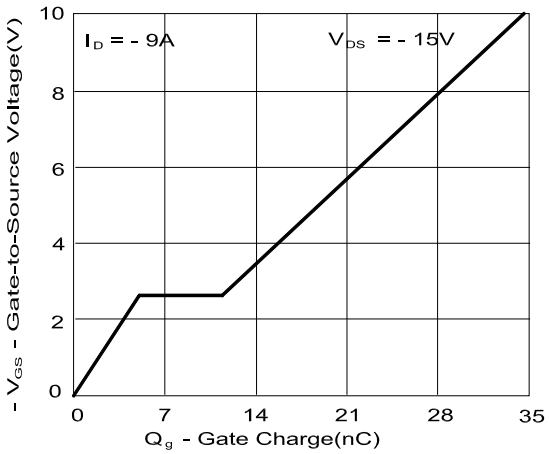
Transfer Characteristics



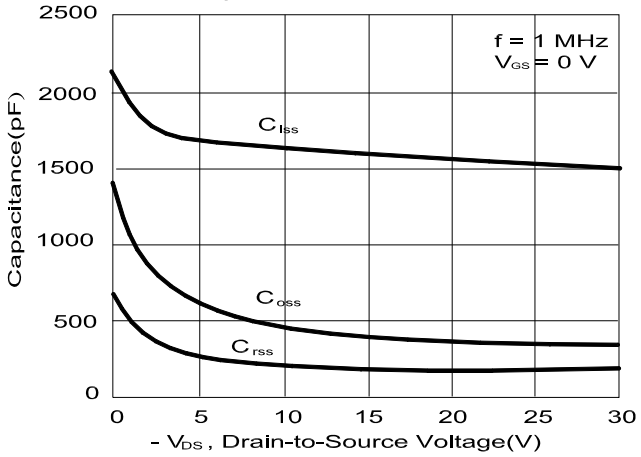
Body Diode Forward Voltage Variation with Source Current and Temperature



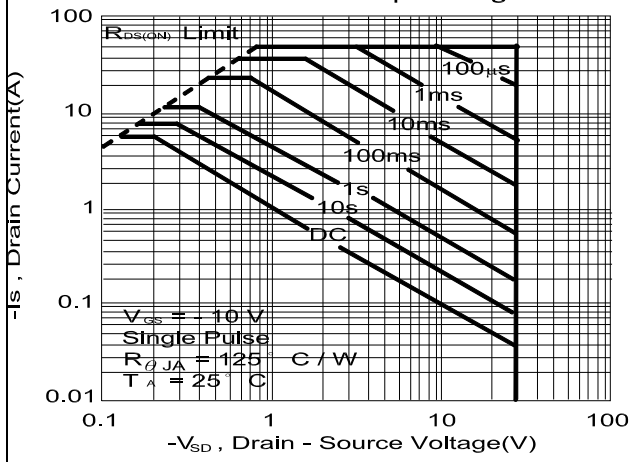
Gate Charge Characteristics



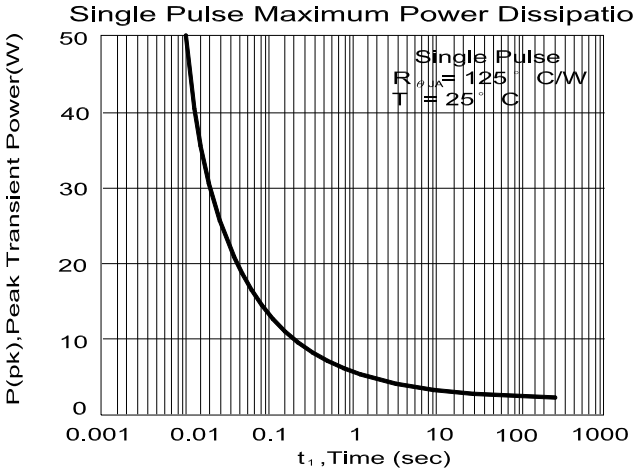
Capacitance Characteristics



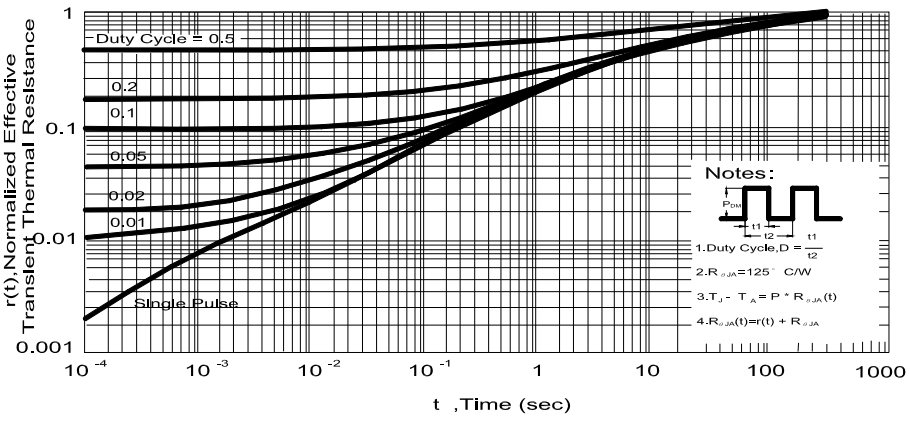
Maximum Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



SOIC-8(D) MECHANICAL DATA

Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8	4.9	5.0	H	0.4	0.715	0.83
B	3.8	3.9	4.0	I	0.19	0.22	0.25
C	5.8	6.0	6.2	J	0.25	0.375	0.5
D	0.33	0.445	0.51	K	0°	4°	8°
E		1.27		L			
F	1.25	1.375	1.62	M			
G	0.1	0.175	0.25	N